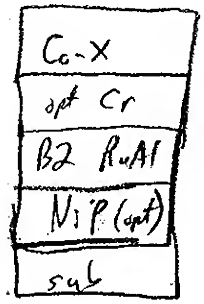
Seagate

3/7/01
12/20/01

10/022,728



(11.0) crystal

oxidized, textured

spec • Replacement App pgs 4+5 w/o highlighting
• "USEA 2758" – replace with U.S. Patent office serial number

admissions
• OR ~1.5 have > S/N ratio than OR=1.0
• Cr (200) promotes Co (11.0)
B2 (200)

~742 A1

102: c1, 3, 6, 9, 10 – 16, 20
103: c2 (sub = mech. textured; OR > ~1.05)
c4+17 ^{textured} (oxidized NiP on non-metallic substrate)
c5 (surface oxidized NiP on Al alloy substrate)
+19^{17} c7^{4} (12-50 at% P, 0.5-50 at% surface oxygen)
c8^{7} (NiP = 50-200,000 Å)
c18 (elect. plated oxidized NiP on Al alloy, plus textured)

c2) ivo Lal et al + Okumura et al
c4, 7, 8, 17, 19) ivo Chen et al '795 + Chen et al '370
c5, 18, ivo Chen et al (x2) above + Obara et al ~949 A1
c18) as c5 + ivo Okumura et al + Lal et al

cite – Jones et al, Cao et al, Kanbe et al

• Equiv. of glass to NiP/Al
• texturing of NiP → motiv.
• OR 1.4-1.6 motiv.

(cite)

Kaitu '796 Al

Benefits of circum texturing

(cite)

Jones '809

• OR >1.5 as desired for longitudinal
• textured substrate inc. NiP/Al (harder) or glass

Lal et al '924

oxidizing condition

Chen et al '370

(cite)

• Equiv. of substrates
• Equiv. of plating/sputtering
• texturing NiP induces anisotropy
• control anisotropy to 0.95 - 1.10

(cite)

Cao '033

• equiv. of sputter or plating
• Effect on OR of texture
• motiv. to texture

Okumura '733

Ni_3P (25% P)

Co-mag (11x)
Cr
B2 (200)
Cr (base)
surface Ox. NiP
sub

Chen et al '795

longitudinal media
• NiP oxidized - motiv. and textured - motiv.

Co (1120)
Cr (200)
oxid NiP
sub

Abarra '949 Al